FUTURE ELECTRONICS

FUTURE ELECTRONICS PRESENTS

Power Design Seminars

Discover the latest advances in wide bandgap semiconductors

and the impact on system cost and performance of using SiC, GaN and hybrid Si-SiC ICs and modules

Apply to attend by e-mailing: FPS-EMEA@FutureElectronics.com or via the seminars link at the Technical Resources section of the www.FutureElectronics.com website for your region.

FUTURE Power Solutions

Meet the experts in wide bandgap power semiconductors

SiC (silicon carbide) and GaN (gallium nitride) wide bandgap semiconductor materials are attracting great interest from power engineers because of their superior thermal, switching and power-handling characteristics compared to silicon. Recent steep falls in the price of MOSFETs, diodes and modules based on wide bandgap materials are making them increasingly attractive for mainstream applications in the industrial, automotive, military and aerospace markets.

Future Electronics' new series of day-long seminars will help design engineers to compare the latest wide bandgap components to conventional silicon devices, and to make well-informed decisions about their system-wide impact.

The seminars will run from September 2017 to January 2018, and will take place across many European cities. Engineers from Future Electronics' specialist Future Power Solutions division will lead the technical presentations alongside power design experts from the following component manufacturers: STMicroelectronics, ON Semiconductor, ROHM Semiconductor, Panasonic, RECOM, Murata and Aavid Thermalloy.

Each event will also include a lunchtime technology fair featuring demonstrations from these franchised suppliers of Future Electronics.

By attending the wide bandgap seminar, you can learn about:

- The effect of choosing SiC or GaN components on system performance, size and cost
- Comparing discrete SiC components with hybrid Si-SiC and full SiC modules
- Implications for passive component selection and thermal management
- How to migrate successfully from superjunction MOSFETs to SiC or GaN MOSFETs
- Special considerations in the implementation of gate drivers and auxiliary power supply design

Where and When

Date	Location
19/9/2017	Gothenburg, Sweden
3/10/2017	Rennes, France
10/10/2017	Madrid, Spain
11/10/2017	San Sebastian, Spain
22/11/2017	Helsinki, Finland
29/11/2017	Vejle, Denmark
31/1/2018	Padova, Italy
08/02/2018	Lyon, France

BOOK NOW: access to the seminars is by prior application only and spaces are limited.
To reserve your place e-mail: FPS-EMEA@FutureElectronics.com

Click here to go to the Power Seminars registration page

FUTURE Power Solutions

POWER SEMINAR PARTNERS

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